

INTERNATIONAL STANDARD

IEC
60747-1

Second edition
2006-02

Semiconductor devices –

**Part 1:
General**

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CONTENTS

FOREWORD.....	4
1 Scope.....	6
2 Normative references	6
3 Terms and definitions	6
3.1 Device structure	6
3.2 Elements and circuits	7
3.3 Thermal characteristics	8
3.4 Noise	9
3.5 Conversion loss.....	9
3.6 Stability of characteristics.....	10
4 Letter symbols.....	10
4.1 General.....	10
4.2 Letter symbols for currents, voltages and powers	11
4.3 Letter symbols for signal ratios expressed in dB.....	13
4.4 Letter symbols for other electrical properties	14
4.5 Letter symbols for other properties	15
4.6 Presentation of limit values	17
5 Essential ratings and characteristics.....	18
5.1 General.....	18
5.2 Relationship between conditions of use, ratings and characteristics	18
5.3 Standard format for the presentation of published data.....	19
5.4 Type identification	19
5.5 Terminal and polarity identification	19
5.6 Electrical ratings and characteristics	20
5.7 Cooling conditions.....	20
5.8 Recommended temperatures.....	21
5.9 Recommended voltages and currents.....	21
5.10 Mechanical ratings (limiting values).....	21
5.11 Mechanical characteristics	22
5.12 Multiple devices having a common encapsulation.....	22
6 Measuring methods	23
6.1 General.....	23
6.2 Alternative methods of measurement.....	23
6.3 Measurement accuracy	24
6.4 Protection of devices and measuring equipment.....	24
6.5 Thermal conditions for measuring methods	24
6.6 Accuracy of measuring circuits	25
7 Acceptance and reliability of discrete devices.....	27
7.1 General.....	27
7.2 Electrical endurance tests	27
8 Electrostatic-sensitive devices.....	31
8.1 Label and symbol	31
8.2 Test methods for semiconductor devices sensitive to voltage pulses of short duration.....	32

9	Product discontinuance notification	32
9.1	Definitions	32
9.2	General aspects for discontinuation.....	33
9.3	Information for the discontinuance notification.....	33
9.4	Notification	33
9.5	Retention	34
	Annex A (informative) Presentation of IEC 60747 and IEC 60748	35
	Annex B (informative) Clause cross-references from the previous edition of IEC 60747-1	39
	Bibliography.....	
	Figure 1 – Example of the application of the rules to a periodic current.....	11
	Figure 2 – Derating curve	28
	Figure 3 – Symbol to be used for the electrostatic sensitive devices that require special handling.....	31
	Table 1 – Presentation of limit values with the two conventions	18
	Table 2 – Failure rate operating conditions	29

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

SEMICONDUCTOR DEVICES –

Part 1: General

FOREWORD

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International Standard IEC 60747-1 has been prepared by IEC technical committee 47: Semiconductor devices.

This second edition of IEC 60747-1 cancels and replaces the first edition (1983) and its amendments 1 (1991), 2 (1993) and 3 (1996).

The main changes with respect to the previous edition are listed below.

- a) The terminology which is now given in the IEC (or which was in conflict with the IEC) has been omitted.
- b) There has been a general revision of guidance on essential ratings and characteristics.
- c) The distinction between general and reference methods of measurement has been removed.
- d) A clause on product discontinuation notice has been added.

The text of this standard is based on the following documents:

FDIS	Report on voting
47/1841/FDIS	47/1848/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The list of all parts of IEC 60747 series, under the general title *Semiconductor devices*, can be found on the IEC website.

The committee has decided that the contents of this publication will remain unchanged until the maintenance result date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

The contents of the corrigendum of September 2008 have been included in this copy.

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SEMICONDUCTOR DEVICES –

Part 1: General

1 Scope

This part of IEC 60747 gives the general requirements applicable to the discrete semiconductor devices and integrated circuits covered by the other parts of IEC 60747 and IEC 60748 (see Annex A).

2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60027 (all parts), *Letter symbols to be used in electrical technology*

IEC 60050-521, *International Electrotechnical Vocabulary (IEV) – Part 521: Semiconductor devices and integrated circuits*

IEC 60050-702, *International Electrotechnical Vocabulary (IEV) – Part 702: Oscillations, signals and related devices*

IEC 60068 (all parts), *Environmental testing*

IEC 60191-2, *Mechanical standardization of semiconductor devices – Part 2: Dimensions*

IEC 60747 (all parts), *Semiconductor devices*

IEC 60748 (all parts), *Semiconductor devices – Integrated circuits*

IEC 60749-26, *Semiconductor devices – Mechanical and climatic test methods – Part 26: Electrostatic discharge (ESD) sensitivity testing – Human body model (HBM)*

IEC 61340 (all parts), *Electrostatics*

QC 001002 (all parts), *IEC Quality Assessment Systems for Electronic Components (IECQ) – Rules of procedure*

ISO 9000, *Quality management systems – Fundamentals and vocabulary*

3 Terms and definitions

For the purposes of this document, the terms and definitions given in IEC 60050-521 and IEC 60050-702, as well as the following, apply.

3.1 Device structure

3.1.1

pad

area on a chip (die) to which a connection to the chip (die) can be made

3.1.2

bonding wire

wire that is bonded to a chip (die) bonding pad in order to connect the chip (die) to any other point within the device package

3.1.3

base (of a package)

part of the package on which a chip (die) can be mounted

3.1.4

cap, can, lid, plug

part of a cavity package that completes its enclosure

NOTE The particular term used depends on the package design.

3.1.5

anode terminal (of a semiconductor diode, excluding current-regulator diodes)

terminal connected to the P-type region of the PN junction or, when more than one PN junction is connected in series with the same polarity, to the extreme P-type region

NOTE For voltage-reference diodes; if temperature-compensating diodes are included, these are ignored in the determination of the anode terminal.

3.1.6

cathode terminal (of a semiconductor diode, excluding current-regulator diodes)

terminal connected to the N-type region of the PN junction or, when more than one PN junction is connected in series with the same polarity, to the extreme N-type region

NOTE For voltage-reference diodes; if temperature-compensating diodes are included, these are ignored in the determination of the cathode terminal.

3.1.7

anode terminal (of a current-regulator diode)

terminal to which current flows from the external circuit when the diode is biased to operate as a current regulator

3.1.8

cathode terminal (of a current-regulator diode)

terminal from which current flows into the external circuit when the diode is biased to operate as a current regulator

3.2 Elements and circuits

3.2.1

passive circuit element

circuit element primarily contributing resistance, capacitance, inductance, ohmic inter-connection, wave-guiding, or a combination of these, to a circuit function

NOTE For example, resistors, capacitors, inductors, passive filters, interconnections.

3.2.2

active circuit element

circuit element that contributes other qualities to a circuit function than a passive circuit element, for example, rectification, switching, gain, conversion of energy from one form to another

NOTE 1 Examples for devices with active circuit elements are diodes, transistors, active integrated circuits, light-sensing or light-emitting devices.

NOTE 2 Active physical circuit elements may also be used to act as passive physical circuit elements only, for example, to contribute resistance and/or capacitance to a circuit function temperature.

3.2.3

reference-point temperature

temperature at a specified point on, near or within a device

3.2.4

case temperature

temperature of a reference point, on or near the surface of the case

NOTE For smaller devices, if the specified reference point is not located on the case but somewhere else on the device (for example, on one of the terminals), then the temperature at this place may be called the "reference-point temperature". However, devices rated with reference to this temperature are still called "case-rated devices".

3.2.5

storage temperature

temperature at which the device may be stored without any voltage being applied

3.3 Thermal characteristics

3.3.1

thermal derating factor

factor by which the power dissipation rating must be reduced with increase of reference point temperature

3.3.2

equivalent thermal network

theoretical equivalent circuit that simulates the thermal resistances, thermal capacitances and sources of heat flow of a semiconductor device (or integrated circuit), which gives a representation of thermal conditions and temperature behaviour under electrical load and which may be used for temperature calculations

NOTE 1 It is assumed that the total heat flow, caused by the power dissipation, is flowing through this equivalent thermal network.

NOTE 2 Where heat is generated at more than one point in a device, the equivalent thermal networks will need to include each source if the heat flow is to correspond to the total power dissipation occurring in the semiconductor device (or integrated circuit).

3.3.3

transient thermal impedance

quotient of

- a) the change in temperature difference between two specified points or regions at the end of a time interval, and
- b) the step-function change in power dissipation beginning at that time interval which causes the change in temperature difference

NOTE The term used in practice must indicate the two specified points or regions, for example, as in "junction-case transient thermal impedance". The use of the shortened term "transient thermal impedance" is permitted only if no ambiguity is likely to occur.

3.3.4

thermal impedance under pulse conditions

quotient of

- a) the difference between the maximum virtual temperature caused by the pulse power and the temperature of a specified external reference point, and
- b) the amplitude of the power dissipation in the device produced by a specified periodic sequence of rectangular pulses

NOTE 1 The initial transient phenomena are ignored and zero continuous power dissipation is assumed.

NOTE 2 The thermal impedance under pulse conditions is given as a function of the duration of the pulses with the duty factor as a parameter.

3.4 Noise

3.4.1

reference-noise temperature

absolute temperature (in kelvins) to be assumed as a noise temperature at the input ports of a network when calculating certain noise parameters, and for normalizing purposes

NOTE It has not been possible to achieve a consensus on a single standard reference noise temperature, although no values below 290 K or above 300 K were found to be in use.

3.4.2

overall average noise figure (of a mixer diode and an I.F. amplifier)

average noise figure of the cascaded combination of a mixer and an I.F. amplifier

3.4.3

standard overall average noise figure (of a mixer diode and an I.F. amplifier)

overall average noise figure, when the average noise figure of the I.F. amplifier is a specified standard value (usually 1,5 dB) and the passband of the I.F. amplifier is sufficiently narrower than that of the mixer so that the mixer conversion loss and output noise temperature are essentially constant over the I.F. passband

3.4.4

output noise ratio

ratio of the noise temperature of an output port to the reference noise temperature, when the noise temperature of all input terminations is at the reference noise temperature at all frequencies that contribute to the output noise

3.4.5

equivalent input noise voltage (of a two-port)

voltage of an ideal voltage source (having an internal impedance equal to zero) in series with the input terminals of the device that represents the part of the internally generated noise that can properly be represented by a voltage source

NOTE In the definition, the equivalent input noise current, which would be needed for a complete and precise description of the device noise, is neglected. If the external source impedance is zero, the noise voltage represents the total noise.

3.4.6

equivalent input noise current (of a two-port)

current of an ideal current source (having an internal impedance equal to infinity) in parallel with the input terminals of the device that represents the part of the internally generated noise that can properly be represented by a current source

NOTE In this definition, the equivalent input noise voltage, which would be needed for a complete and precise description of the device noise, is neglected. If the external source impedance is infinite, the noise current represents the total noise.

3.5 Conversion loss

3.5.1

conversion loss (of a mixer, mixer diode or harmonic generator)

ratio of available input power at a single-signal frequency to the available single-signal frequency output power, not including intrinsic mixer noise or power converted from other than the signal-input frequency

3.5.2

conversion insertion loss (of a mixer, mixer diode or harmonic generator)

ratio of available input power at a single-signal frequency to the delivered single-signal frequency output power, not including intrinsic mixer noise or power converted from other than the signal-input frequency

3.6 Stability of characteristics

3.6.1

drift

difference between the final value of a characteristic at the end of a specified long period and the initial value, all other operating conditions being held constant

NOTE The use of the term "drift" to refer to the immediate change of a characteristic in direct response to changed operating conditions (for example, temperature) is deprecated.

3.6.2

relative drift

ratio of

- drift of the characteristic, to
- initial value of the characteristic

NOTE See note to 0.

3.6.3

instability range

difference between the extreme values of the characteristic observed either continuously or repeatedly during a specified period, all other operating conditions being held constant

3.6.4

relative instability range

quotient of

- the instability range of the characteristic, and
- the initial value of the characteristic

4 Letter symbols

4.1 General

This clause provides a system of letter symbols for the properties used in the field of discrete devices and integrated circuits. Additional letter symbols, for specific categories may be given in Clause 4 of the other parts of IEC 60747 and IEC 60748. Where there is any conflict, the symbols given in the latter parts apply within the part.

The general standards given in IEC 60027 are applicable, except where this clause differs, in which case this clause should be followed. Some letter symbols or rules for composing complex letter symbols have been specifically approved for the purposes of IEC 60747 and IEC 60748.

NOTE Definitions of the terms used in this clause can be found in Clause 3 of this or the other parts of IEC 60747 and IEC 60748.